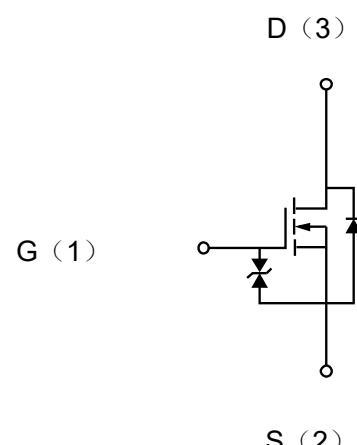


## Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
20	0.2@ V <sub>GS</sub> =4.5V	1
	0.25@ V <sub>GS</sub> =2.5V	
	0.31@ V <sub>GS</sub> =1.8V	



## Absolute maximum rating@25°C

Parameter	Symbol	Value	Units
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	1	A
	I <sub>DP</sub>	4	
Total power dissipation	P <sub>D</sub>	140	mW
Channel temperature	T <sub>CH</sub>	150	°C
Range of storage temperature	T <sub>STG</sub>	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limits	Units
Channel to ambient	R <sub>th(ch-a)</sub>	800	°C/W

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	20		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 8\text{V}$	-	-	10	$\mu\text{A}$
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	0.5	-	1.1	V
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS} = 4.5\text{V}, I_D = 650\text{mA}$	-	0.2	0.25	$\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 450\text{mA}$	-	0.25	0.3	$\Omega$
		$V_{GS} = 1.8\text{V}, I_D = 250\text{mA}$		0.31	0.45	$\Omega$
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 300\text{mA}$	395			ms
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 10\text{V}, f = 1\text{MHz}$	-	30		pF
Output Capacitance	$C_{oss}$		-	13		pF
Reverse Transfer Capacitance	$C_{rss}$		-	3		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{V}, V_{GS} = 4.0\text{V}, R_G = 10\Omega, R_L = 67\Omega, I_D = 150\text{mA}$	-	7		ns
Turn-Off Delay Time	$t_{d(off)}$		-	23		ns
Turn-On Rise Time	$t_r$		-	15		ns
Turn-On Fall Time	$t_f$		-	15		ns
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{V}, I_S = 100\text{mA}$		-	1.2	V

## Typical Characteristics

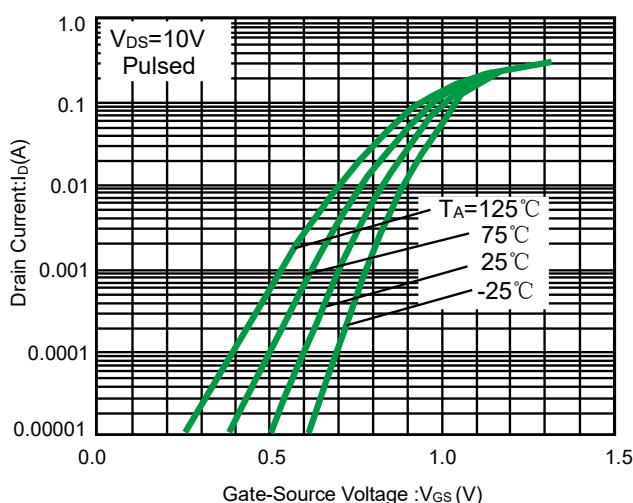


Fig 1. Typical transfer Characteristics

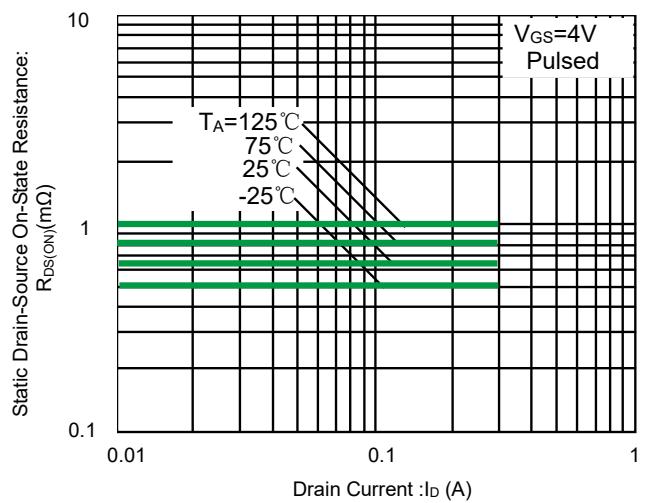


Fig 2. Static drain-source on-state resistance vs. drain current (I )

## N-Channel MOSFET

PNM523T201E0

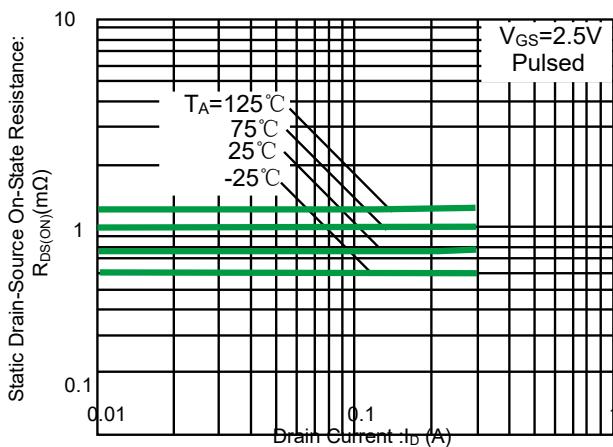


Fig 3. Static drain-source on-state resistance  
Vs. drain current (II)

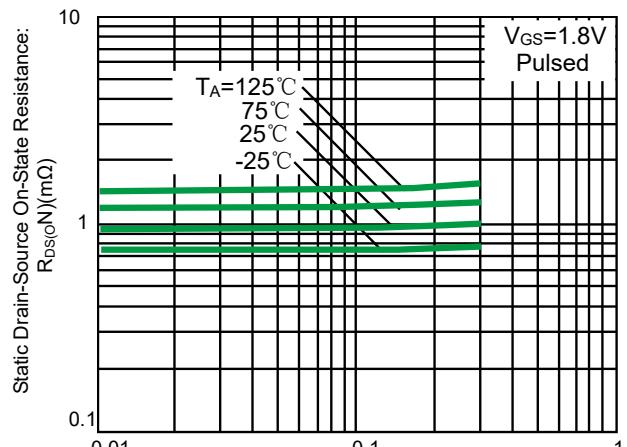


Fig 4. Static drain-source on-state resistance vs.  
drain current (III)

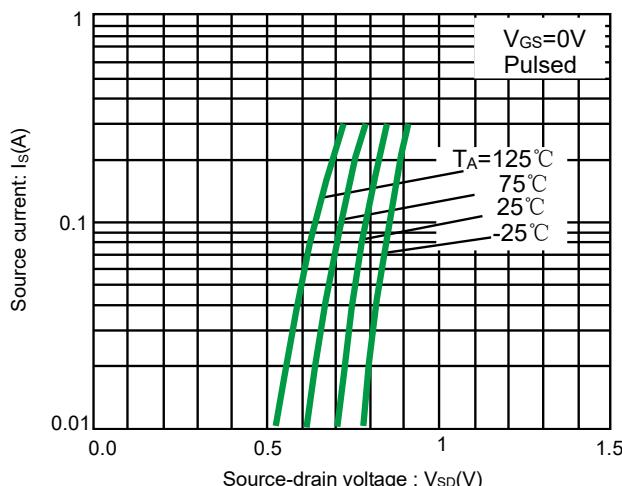


Fig 5. Source current vs. source-drain voltage

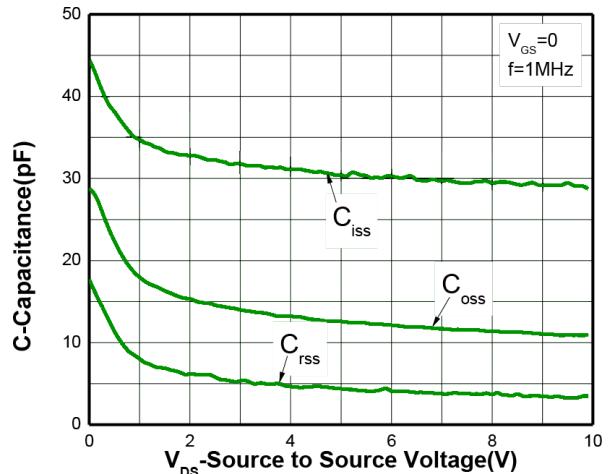


Fig 6. Typical capacitance vs. drain-source voltage

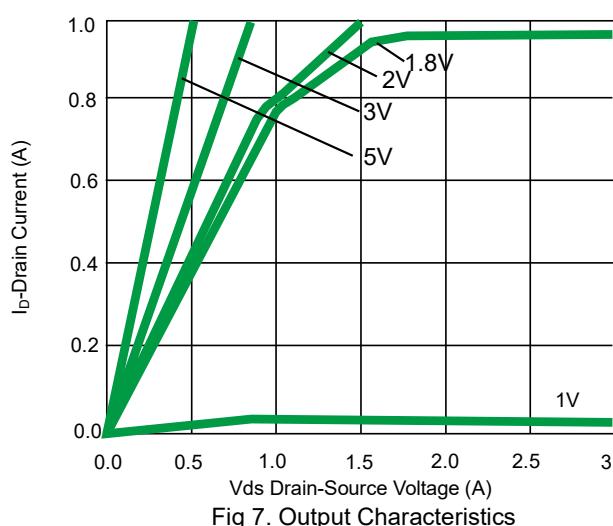


Fig 7. Output Characteristics

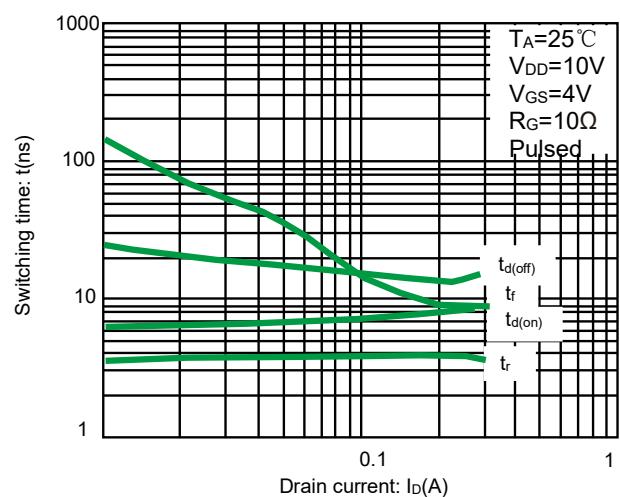


Fig 8. Switching characteristics

## N-Channel MOSFET Switching characteristics measurement circuit

PNM523T201E0

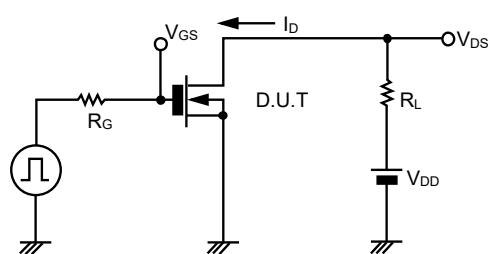


Fig.8 Switching time measurement circuit

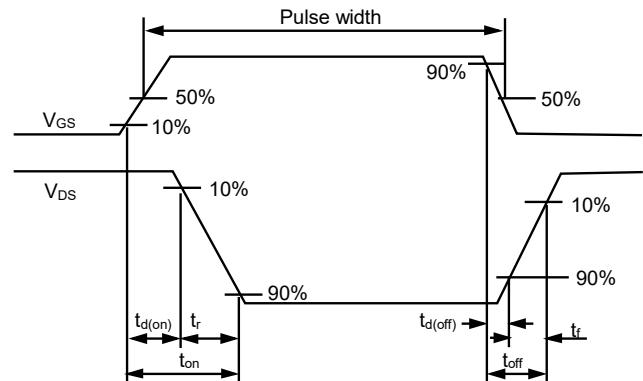
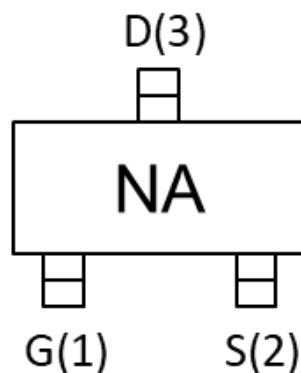
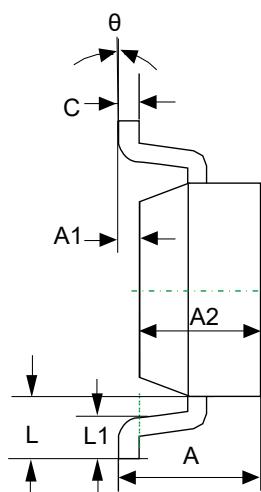
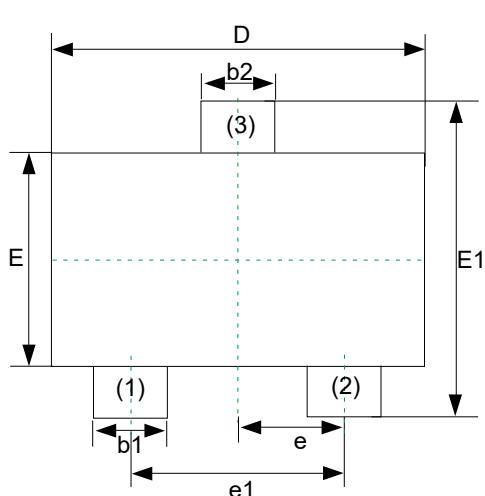


Fig.9 Switching time waveforms

## Marking information



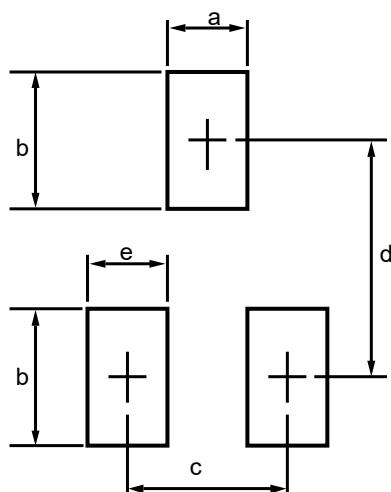
## Product dimension (SOT-523)



## N-Channel MOSFET

PNM523T201E0

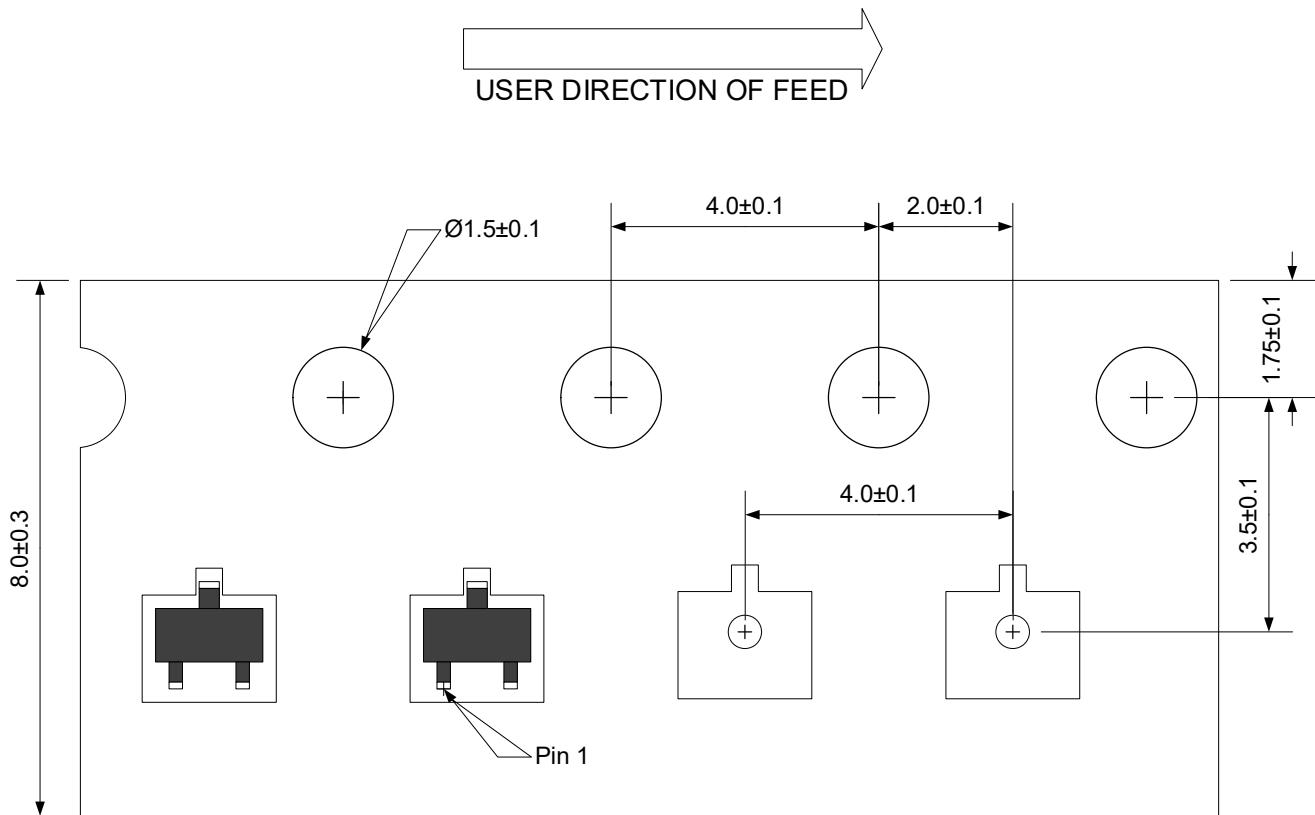
Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



Dim	Millimeters	
	MIN	MAX
a	--	0.5
b	--	0.6
c	--	1.0
d	--	1.24
e	--	0.4

## Ordering information

Device	Package	Shipping
PNM523T201E0	SOT-523 (Pb-Free)	3000 / Tape & Reel



Unit:mm

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